# **NGTD17T65F2**

## **IGBT** Die

Trench Field Stop II IGBT Die for motor drive and inverter applications.

## Features

- Extremely Efficient Trench with Field Stop Technology
- Low V<sub>CE(sat)</sub> Loss Reduces System Power Dissipation

## **Typical Applications**

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

### MAXIMUM RATINGS

Parameter	Symbol	Value	Unit		
Collector–Emitter Voltage, $T_J = 25^{\circ}C$	V <sub>CE</sub>	650	V		
DC Collector Current, limited by $T_{J(\text{max})}$	۱ <sub>C</sub>	(Note 1)	A		
Pulsed Collector Current (Note 2)	I <sub>C, pulse</sub>	160	А		
Gate-Emitter Voltage	$V_{GE}$	±20	V		
Maximum Junction Temperature	ТJ	-55 to +175	°C		
Short Circuit Withstand Time, $V_{GE}$ = 15 V, $V_{CE}$ = 500V, $T_J$ $\leq$ 150°C	T <sub>SC</sub>	5.0	μs		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Depending on thermal properties of assembly.

2.  $T_{pulse}$  limited by  $T_{jmax}$ , 10 µs pulse,  $V_{GE}$  = 15 V.

## **MECHANICAL DATA**

Parameter	Value	Unit	
Die Size	3915 x 4115	μm <sup>2</sup>	
Emitter Pad Size	See die layout	μm <sup>2</sup>	
Gate Pad Size	585 x 600	μm <sup>2</sup>	
Die Thickness	3	mils	
Wafer Size	150	mm	
Top Metal	4 μm AISI		
Back Metal	2 μm TiNiAg		
Max possible chips per wafer	778		
Passivation frontside	Oxide-Nitride		
Reject ink dot size	25 mils		
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28°C, 30–65%RH	Type: Die on tape in ring–pack Storage time: < 3 months		

### **ORDERING INFORMATION**

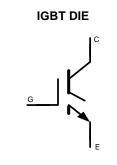
Device	Inking?	Shipping
NGTD17T65F2WP	Yes	Bare Wafer on Tape
NGTD17T65F2SWK	Yes	Sawn Wafer on Tape



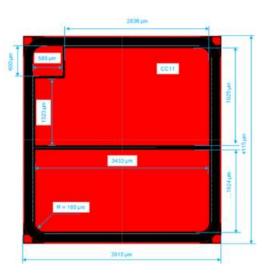
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 $V_{RCE} = 650 V$  $I_{C}$  = Limited by  $T_{J(max)}$ 



**DIE OUTLINE** 



## NGTD17T65F2

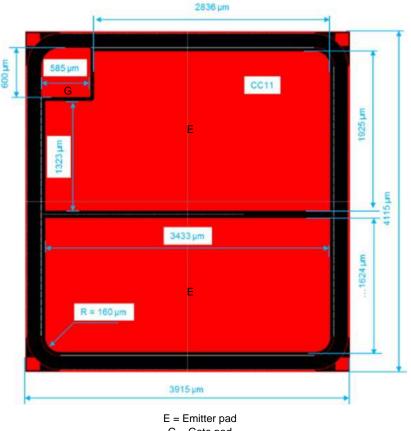
#### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ , unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Units
STATIC CHARACTERISTICS						•
Collector-Emitter Breakdown Voltage	$V_{GE}$ = 0 V, I <sub>C</sub> = 500 $\mu$ A	V <sub>(BR)CES</sub>	650			V
Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 40 A	V <sub>CE(sat)</sub>		1.7	2.0	V
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 350 \ \mu A$	V <sub>GE(TH)</sub>	4.5	5.5	6.5	V
Collector-Emitter Cutoff Current	$V_{GE} = 0 V, V_{CE} = 650 V$	I <sub>CES</sub>			0.5	mA
Gate Leakage Current	$V_{GE}$ = 20 V, $V_{CE}$ = 0 V	I <sub>GES</sub>			200	nA
DYNAMIC CHARACTERISTICS						
Innut Consoltance		0		4060		~ <b>Г</b>

Input Capacitance		Cies	4060	pF	ĺ
Output Capacitance	V <sub>CE</sub> = 20 V, V <sub>GE</sub> = 0 V, f = 1 MHz	C <sub>oes</sub>	179	pF	ĺ
Reverse Transfer Capacitance		C <sub>res</sub>	115	pF	ĺ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## DIE LAYOUT



G = Gate padAll dimensions in  $\mu m$ 

## **Further Electrical Characteristic**

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

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